BT152-500RT



SCR

Rev. 2 — 9 June 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated Silicon Controlled Rectifier in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high junction temperature capability and high thermal cycling performance.

1.2 Features and benefits

- High junction temperature capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

1.3 Applications

- Ignition circuits
- Motor control

- Protection circuits e.g. SMPS inrush current
- Voltage regulation

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	500	V
V_{RRM}	repetitive peak reverse voltage		-	-	500	V
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	-	-	220	Α
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	200	Α
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 122 °C; see <u>Figure 3</u>	-	-	13	Α
I _{T(RMS)}	RMS on-state current	half sine wave; see Figure 1; see Figure 2	-	-	20	Α
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } 100 \text{ mA;}}$	-	3	32	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		. 51
2	Α	anode	mb	A H K
3	G	gate		G sym037
mb	Α	mounting base; connected to anode	SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT152-500RT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

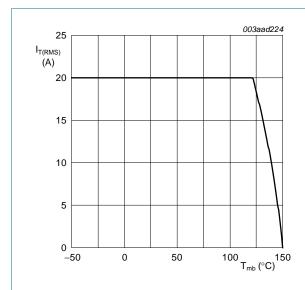
4. Limiting values

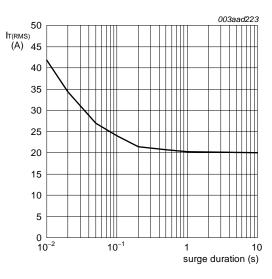
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage)	-	500	V
V_{RRM}	repetitive peak reverse voltage		-	500	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 122 °C; see <u>Figure 3</u>	-	13	Α
I _{T(RMS)}	RMS on-state current	half sine wave; see Figure 1; see Figure 2	-	20	Α
I _{TSM} non-repetitive pea current	non-repetitive peak on-state	half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$	-	220	Α
	current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see Figure 4; see Figure 5	-	200	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	200	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 50 A; I_G = 200 mA; dI_G/dt = 200 mA/ μ s	-	200	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

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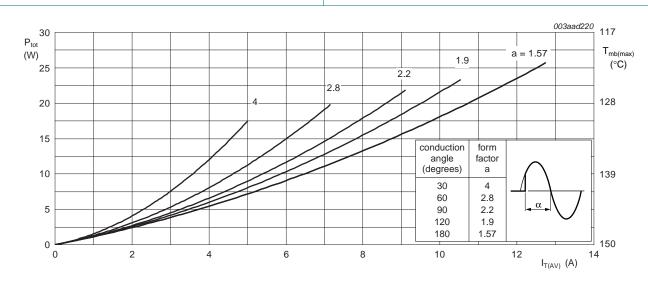




 $f = 50 \text{ Hz}; T_{\text{mb}} = 122 \text{ °C}$

Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values



a =form factor $= I_{T(RMS)} / I_{T(AV)}$

Fig 3. Total power dissipation as a function of average on-state current; maximum values

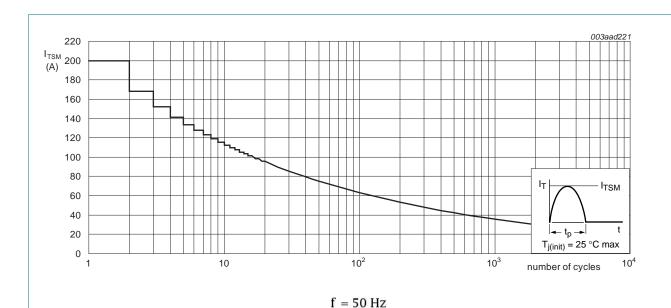


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

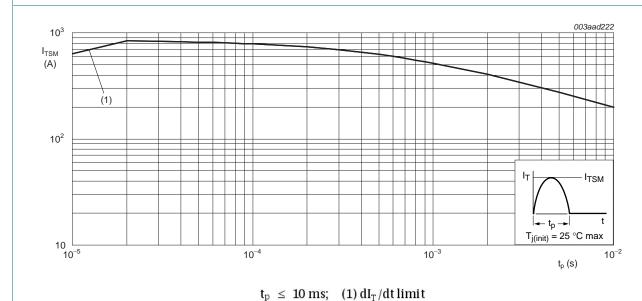


Fig 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 6	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

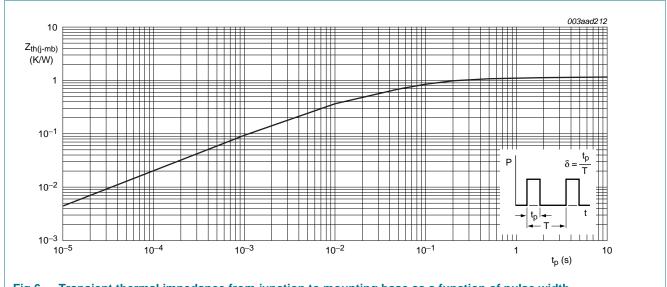


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; } T_j = 25 \text{ °C; see}$ Figure 7	-	3	32	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	25	80	mA
I _H	holding current	T _j = 25 °C; see <u>Figure 9</u>	-	15	60	mΑ
V_{T}	on-state voltage	$I_T = 40 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{}$	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; } T_j = 25 \text{ °C; see}$ Figure 11	-	0.6	1.5	V
		V_D = 500 V; I_T = 100 mA; T_j = 125 °C; see <u>Figure 11</u>	0.25	0.4	-	V
I_D	off-state current	$V_D = 500 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.2	1	mΑ
I _R	reverse current	T _j = 125 °C; V _R 500 V	-	0.2	1	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 335 V; T_j = 125 °C; exponential waveform; gate open circuit; see Figure 12	200	300	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = 500 \text{ V}; I_G = 100 \text{ mA}; $ $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs
t _q	commutated turn-off time	$V_{DM} = 335 \text{ V; } T_j = 125 \text{ °C; } I_{TM} = 20 \text{ A;}$ $V_R = 25 \text{ V; } (dI_T/dt)_M = 30 \text{ A/µs;}$ $dV_D/dt = 50 \text{ V/µs; } R_{GK} = 100 \Omega$	-	70	-	μs

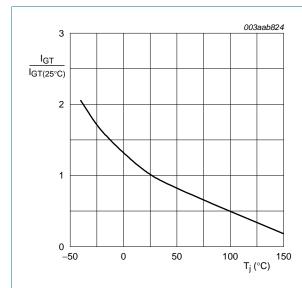


Fig 7. Normalized gate trigger current as a function of junction temperature

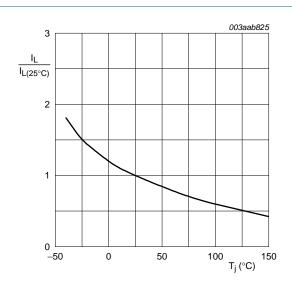
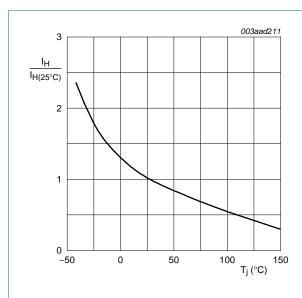


Fig 8. Normalized latching current as a function of junction temperature



10 003aad219 10 0 1 2 N_T(V)

Vo = 1.06 V; Rs = 0.03 Ω

(1) Tj = 150 °C; typical values

(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

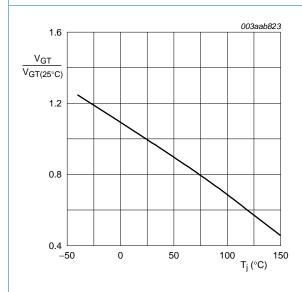
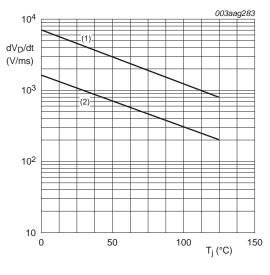


Fig 10. On-state current as a function of on-state voltage

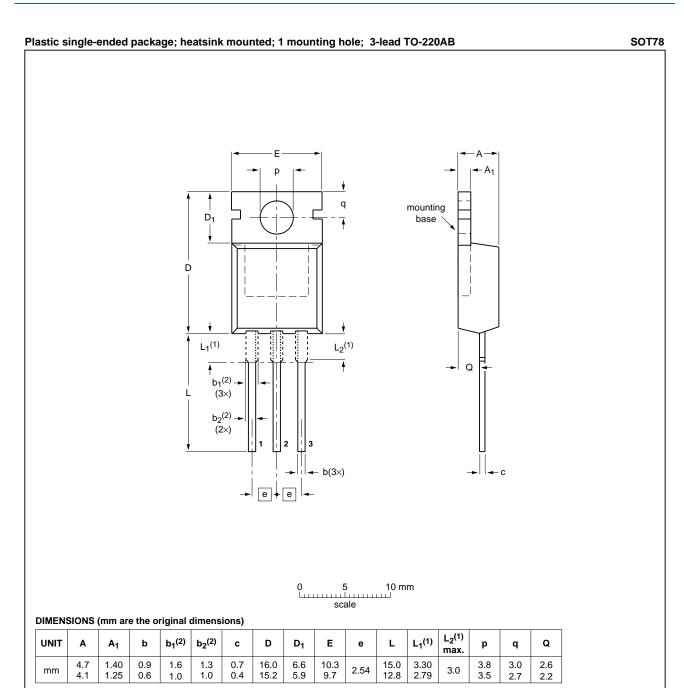


(1) $R_{GK} = 100 \Omega$ (2) Gate open circuit

Fig 11. Normalized gate trigger voltage as a function of junction temperature

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION		REFER	ENCES	EUROPEAN ISSUE DAT	ISSUE DATE
	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 13. Package outline SOT78 (TO-220AB)

BT152-500RT

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT152-500RT v.2	20110609	Product data sheet	-	BT152-500RT v.1
Modifications:	 Various chang 	ges to content.		
BT152-500RT v.1	20090512	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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